

ABSTRACT

Disclosed is a method for forming bit line and bit line contact structure. Based on a semi-finished structure with a poly plug filled in a contact window, the method of the Invention comprises steps of removing some of the oxide layer so that the plug protrudes, oxidizing the exposed region of the protruding portion of the plug, removing the oxidized portion of the plug, forming a first dielectric layer to the upper surface of the resultant structure , wherein the upper surface of the plug is exposed, forming a second dielectric layer to the upper surface of the first dielectric layer including the upper surface of the plug, forming photoresist on the second dielectric layer, then performing exposing, developing and etching to form a trench of a predetermined pattern, and filling metal into the trench to form a bit line.